BTA412Y-600B

3Q Hi-Com Triac

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	1000	-	-	V/µs
		V_{DM} = 402 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	600	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 12 A; dV _{com} /dt = 20 V/µs; (snubberless condition); gate open circuit	20	-	-	A/ms
		$\label{eq:VD} \begin{array}{l} V_{D} = 400 \; V; \; T_{j} = 150 \; ^{\circ}C; \; I_{T(RMS)} = 12 \; A; \\ dV_{com}/dt = 20 \; V/\mus; \; (snubberless \\ condition); \; gate \; open \; circuit \end{array}$	8	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2T1
2	T2	main terminal 2		Sym051
3	G	gate		Symoor
mb	n.c.	mounting base; isolated	()())() ()()() ()()()() ()()()() ()()()()() ()()()()()()()()()()()()()()()()()()()()	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BTA412Y-600B	TO-220AB	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220	SOT78D				

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 116 \degree C$; <u>Fig. 1</u> ; Fig. 2; Fig. 3	-	12	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	140	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	153	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	98	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I _{GM}	peak gate current		-	2	А
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

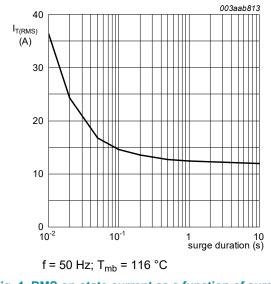


Fig. 1. RMS on-state current as a function of surge duration; maximum values

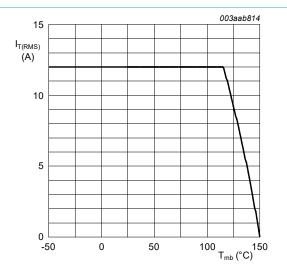
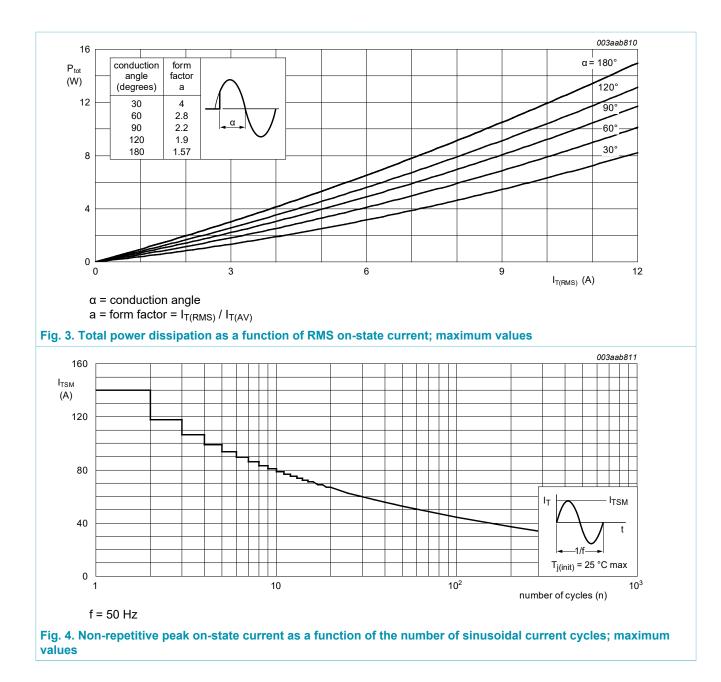


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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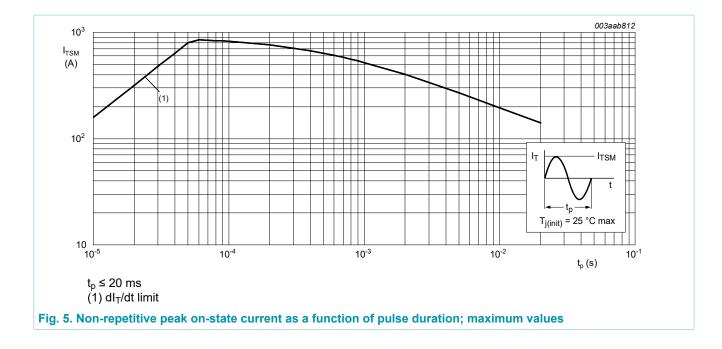
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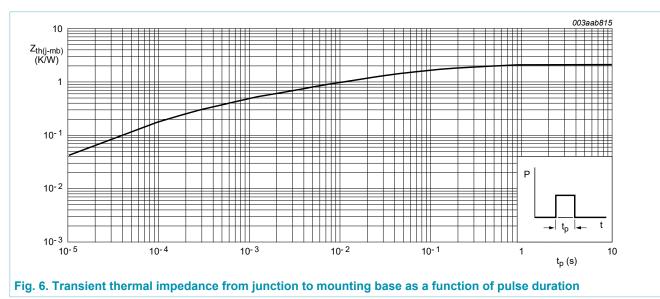


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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; <u>Fig. 6</u>	-	-	2.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



9. Isolation characteristics

Table 6. Isolation	on characteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _{mb} = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _{mb} = 25 °C	-	10	-	pF

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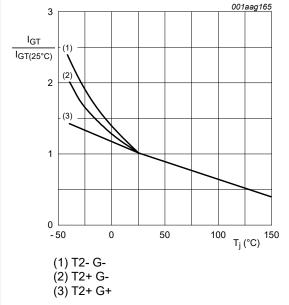
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·				
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	2	-	50	mA
L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	60	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	90	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	60	mA
Н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.8	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C; <u>Fig. 11</u>	0.25	0.4	-	V
D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
		V _D = 600 V; T _j = 150 °C	-	0.4	2	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	1000	-	-	V/µs
		V_{DM} = 402 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	600	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$	20	-	-	A/ms
		$V_D = 400 \text{ V}; \text{ T}_j = 150 \text{ °C}; \text{ I}_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$	8	-	-	A/ms

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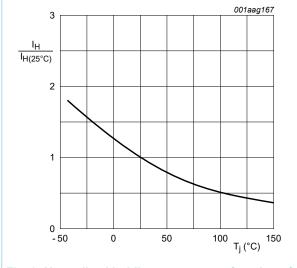
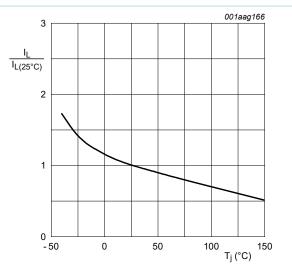
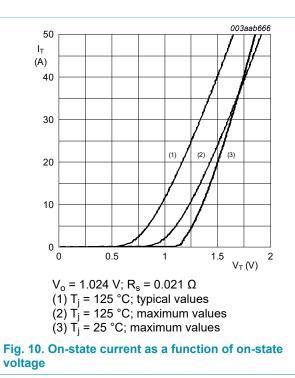


Fig. 9. Normalized holding current as a function of junction temperature



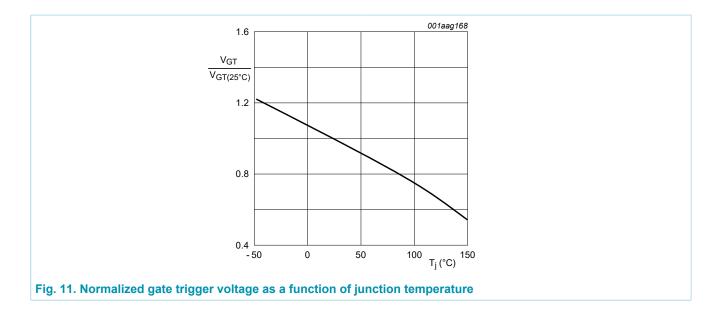




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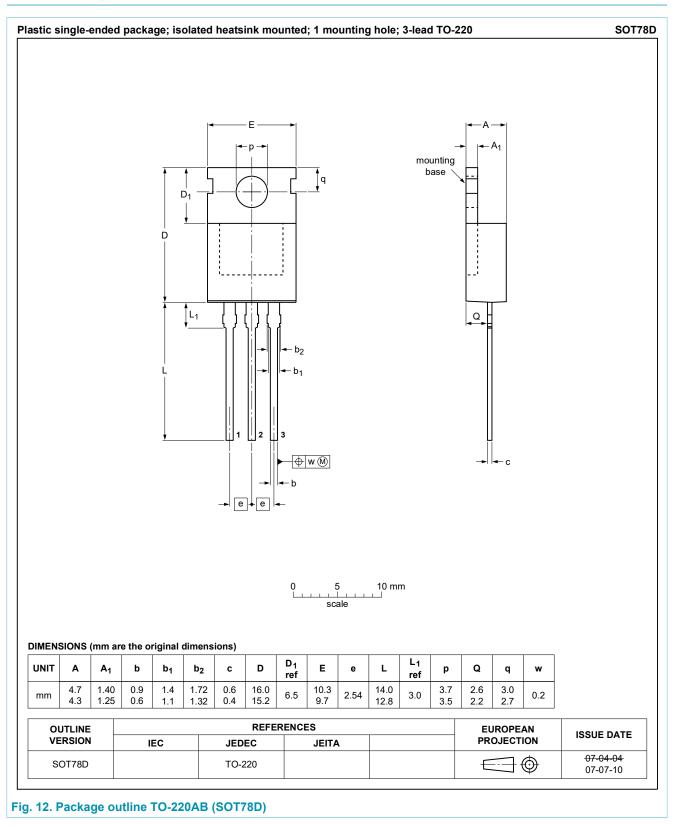
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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